

# Single Stage Primary Side Regulation Flyback Controller with Active PFC for LED 4-Step Dimming and PWM Dimming

### FEATURES

### **Excellent Compatibility and Performance**

- Flickerless 4-Step Dimming and PWM Dimming
- Primary Side Regulation (PSR)
- Constant Current output (+/- 1.5%)
- Universal Input Voltage Range (85V 265V)

### **Energy Efficient**

- Boundary Conduction Mode (BCM) with Valley Switching reduces EMI and enhances Efficiency
- Power Factor Correction (PF > 0.95)
- High Efficiency (> 87%)
- Low Startup Current: 1.0μA
- Low Operating Current: 1.6mA
- Low Quiescent Current: 1.3mA

### **Advanced Protection and Safety Features**

- Open and Short LED Protection
- Cycle by Cycle Current Limit
- VCC Over Voltage Protection (OVP)
- VCC Under Voltage Lockout (UVLO)
- Over Temperature Protection (OTP)

### Package

• SOP-8 Package Available

### DESCRIPTION

The offline primary side control LED lighting controller, SE8326, provides accurate output current, high power factor and low total harmonic distortion. High efficiency is achieved by low operating current and valley turn-on of the primary MOSFET. Constant on-time control is utilized for a better PFC performance, and DCM provides a lower output dimming current.

Two kinds of 4-Step Dimming are provided by SE8326. PWM Dimming can also be adopted.

The multi-protection of SE8326, including open LED protection, short LED protection, cycle by cycle current limit, VCC UVLO and over temperature protection can greatly enhance the system reliability. Current limit threshold is adjusted automatically in a low output condition not only ensures a soft start, but also minimizes the output current when LED is shorted.

### **APPLICATIONS**

- Isolated LED Driver with 4-Step Dimming
- Isolated LED Driver with PWM Dimming

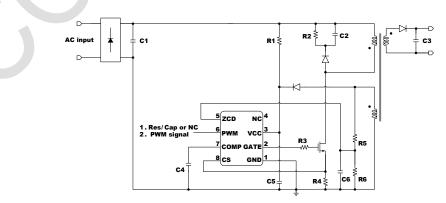


Figure 1. Typical Application

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# FUNCTIONAL BLOCK DIAGRAM

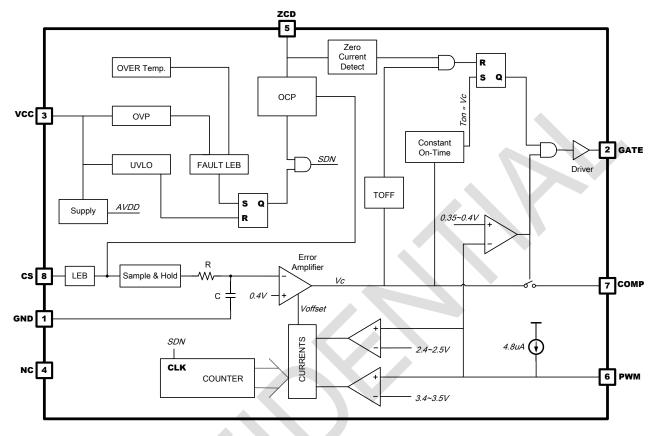


Figure 2. Functional Block Diagram

### **PIN FUNCTIONS**

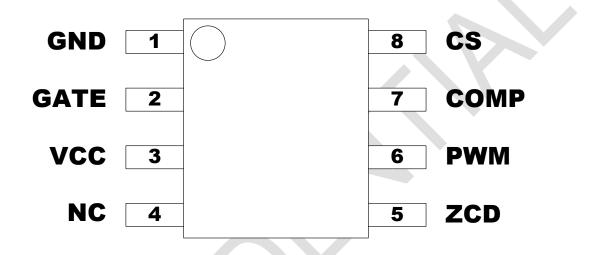
| Pin # | Name | Description                                                                                                                                                                                                              |  |  |
|-------|------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--|--|
| 1     | GND  | Ground.                                                                                                                                                                                                                  |  |  |
| 2     | GATE | Gate drive output pin. The totem pole output stage is able to drive high power MOSFET.                                                                                                                                   |  |  |
| 3     | vcc  | Power supply pin. This pin supply power both for IC operating current and GATE driving current.                                                                                                                          |  |  |
| 4     | NC   | Not connected.                                                                                                                                                                                                           |  |  |
| 5     | ZCD  | Zero current detection pin. Connect this pin through a resistor divider from the auxiliary winding to GND in order to detect the inductor current zero crossing point. This pin also detects the output voltage for OCP. |  |  |
| 6     | PWM  | Dimming mode choosing and PWM signal input.                                                                                                                                                                              |  |  |
| 7     | COMP | Loop Compensation pin. Connect a compensation network to stabilize the loop.                                                                                                                                             |  |  |
| 8     | CS   | Current sense pin. The MOSFET current is sensed via a resistor for constant current regulation and cycle-to-cycle current limit.                                                                                         |  |  |



### **ORDERING INFORMATION**

| ORDERING NUMBER | PINS | PACKAGE |  |
|-----------------|------|---------|--|
| SE8326-SO-L     | 8    | SOP-8   |  |

### PACKAGE REFERENCE



### **ABSOLUTE MAXIMUM RATINGS**

| Item                              | Symbol            | Rating       | Unit |
|-----------------------------------|-------------------|--------------|------|
| GATE Pin Input Voltage            | V <sub>GATE</sub> | -0.3 to 30.0 | V    |
| Power Supply Voltage              | V <sub>cc</sub>   | <30          | V    |
| ZCD Pin Input Voltage             | V <sub>ZCD</sub>  | -0.3 to 7.0  | V    |
| PWM Pin Input Voltage             | V <sub>PWM</sub>  | -0.3 to 7.0  | V    |
| COMP Pin Input Voltage            | V <sub>COMP</sub> | -0.3 to 7.0  | V    |
| CS Pin Input Voltage              | V <sub>CS</sub>   | -0.3 to 7.0  | V    |
| Maximum Junction Temperature      | TJ                | <150         | °C   |
| Storage Temperature               | T <sub>STG</sub>  | -55 to 150   | °C   |
| Lead Temperature (Soldering, 10s) | T <sub>Lead</sub> | <260         | °C   |



# **ELECTRICAL CHARACTERISTICS**

V<sub>CC</sub>=20V, T<sub>A</sub>=+27°C, unless otherwise noted.

| Symbol                | Parameter                                                   | Condition                      | Min. | Тур. | Max. | Unit |
|-----------------------|-------------------------------------------------------------|--------------------------------|------|------|------|------|
| SUPPLY                | <b>SECTION</b> $(T_A = -40^{\circ}C \text{ to } 128)$       | 5°C)                           |      | ·    |      |      |
| V <sub>cc</sub>       | Operating Range                                             |                                | 9    |      | 24   | V    |
| V <sub>CC-ON</sub>    | Turn-On Threshold Voltage                                   |                                | 14   | 16   | 18   | V    |
| $V_{\text{CC-OFF}}$   | Turn-Off Threshold Voltage                                  |                                | 7    | 8    | 9    | V    |
| V <sub>CC-HYS</sub>   | V <sub>CC</sub> Hysteretic Voltage                          |                                | 7    | 8    | 9    | V    |
| I <sub>CC</sub>       | Operating Current                                           | Switch Period = 15µs           | 1.0  | 1.6  | 2.2  | mA   |
| Ι <sub>Q</sub>        | Quiescent Current                                           | No switch                      | 1.0  | 1.4  | 1.9  | mA   |
| I <sub>ST</sub>       | Startup Current                                             | $V_{CC} = V_{CC-ON} - 0.16V$   | 1.1  | 1.1  | 1.8  | μA   |
| $V_{\text{CLAMP}}$    | V <sub>CC</sub> Over-Voltage-Protection                     |                                | 22   | 26   | 30   | V    |
| CONSTA                | NT ON-TIME SECTION (T,                                      | <sub>A</sub> = -40°C to 125°C) |      |      |      |      |
| T <sub>ON-MIN</sub>   | Minimum On Time                                             |                                |      | 400  |      | ns   |
| T <sub>ON-MAX</sub>   | Maximum On Time                                             |                                | 18   | 23   | 28   | μs   |
| DCM SEC               | <b>TION</b> $(T_A = -40^{\circ}C \text{ to } 125^{\circ}C)$ |                                |      |      |      |      |
| T <sub>OFF-MIN</sub>  | Minimum Off Time                                            |                                | 40   | 50   | 60   | μs   |
| ERROR A               |                                                             |                                |      |      |      |      |
| G <sub>M</sub>        | Transconductance                                            |                                |      | 120  |      | µA/V |
| A <sub>EA</sub>       | Voltage Gain                                                | · ·                            |      | 9000 |      | V/V  |
| V <sub>COMP</sub>     | COMP Voltage Range                                          |                                | 0.9  |      | 3.4  | V    |
| I <sub>C-SOURCE</sub> | Max Source Current                                          |                                | 35   | 48   | 65   | μA   |
| I <sub>C-SINK</sub>   | Max Sink Current                                            |                                | -220 | -290 | -360 | μA   |
| GATE DR               | <b>IVER SECTION</b> $(T_A = -40^{\circ}C$                   | C to 125°C)                    |      |      |      |      |
| V <sub>CLAMP</sub>    | Output Clamp Voltage                                        |                                | 11   | 13.5 | 14   | V    |
| I <sub>G-SOURCE</sub> | Max Source Current                                          |                                | 0.97 | 1.2  | 1.4  | Α    |
| I <sub>G-SINK</sub>   | Max Sink Current                                            |                                | -1.2 | -1.7 | -2.1 | А    |
| ZERO CU               | RRENT DETECTOR SECTIO                                       | ON                             |      |      |      |      |
| V <sub>ZCD</sub>      | ZCD Threshold                                               |                                |      | 0.4  |      | V    |
| $V_{ZCD_HYS}$         | ZCD Hysteresis                                              |                                |      | 0.5  |      | V    |
| $T_{OFF}$ -MIN        | Minimum Off Time                                            |                                |      | 3.6  |      | μs   |
| AUTO ST               | ART SECTION                                                 |                                |      |      |      |      |
| T <sub>START</sub>    | Auto Start Time                                             | -40°C < T <sub>A</sub> < 125°C | 100  | 135  | 190  | μs   |

Continued on the following page ...



# **ELECTRICAL CHARACTERISTICS**

 $V_{cc}=20V$ ,  $T_{A}=+27^{\circ}C$ , unless otherwise noted.

| Symbol               | Parameter                                                           | Condition | Min. | Тур. | Max. | Unit |
|----------------------|---------------------------------------------------------------------|-----------|------|------|------|------|
| OVER-CU              | JRRENT PROTECTION SEC                                               | TION      |      |      |      |      |
| V <sub>OCP-H</sub>   | CS High Threshold Voltage for OCP                                   |           |      | 2.5  |      | V    |
| V <sub>OCP-L</sub>   | CS Low Threshold Voltage for OCP                                    |           |      | 1    |      | V    |
| V <sub>HOCP-EN</sub> | ZCD Threshold Voltage to<br>Enable High OCP level                   |           |      | 0.9  |      | V    |
| V <sub>LOCP-EN</sub> | ZCD Threshold Voltage to<br>Enable Low OCP level                    |           |      | 0.6  |      | V    |
| $T_{LEB}$            | CS Sampling Leading-Edge<br>Blanking Time                           |           |      | 215  |      | ns   |
| OVER-VC              | DLTAGE PROTECTION SECT                                              | ΓΙΟΝ      |      |      |      |      |
| V <sub>OVP</sub>     | OVP Threshold Voltage                                               |           |      | 4.4  |      | V    |
| V <sub>OVP_HYS</sub> | OVP Hysteresis Voltage                                              |           |      | 0.6  |      | V    |
| SHORT-C              | URRENT PROTECTION SEC                                               | CTION     |      |      |      |      |
| V <sub>SCP</sub>     | SCP Threshold Voltage                                               |           |      | 4.4  |      | V    |
| $V_{SCP\_HYS}$       | SCP Hysteresis Voltage                                              |           |      | 0.6  |      | V    |
| OVER TE              | MPERATURE PROTECTION                                                | I SECTION |      |      |      |      |
| T <sub>OTP</sub>     | Over Temperature Protection                                         |           | 140  | 150  | 160  | °C   |
| T <sub>OTP-HYS</sub> | OTP Hysteresis                                                      |           | 22   | 25   | 28   | °C   |
| 4-LEVEL              | SWITCH DIMMING SECTION                                              | N         |      |      |      |      |
| V <sub>DIM_H</sub>   | Maximum V <sub>LD</sub> at Low<br>Brightness                        |           | 10   | 11.5 | 13   | V    |
| V <sub>DIM_L</sub>   | Maximum V <sub>LD</sub> at High<br>Brightness                       |           | 4    | 5    | 6    | V    |
| I <sub>DIM</sub>     | $V_{\text{LD}}$ vs. $V_{\text{EA-OFFSET}}$ Slope at High Brightness |           |      | 60   |      | μA   |
| V <sub>EN</sub>      | Enable Voltage on PWM pin                                           |           |      | 2.5  |      | V    |
| I <sub>PWM</sub>     | PWM pin output current                                              |           |      | 4    |      | μA   |

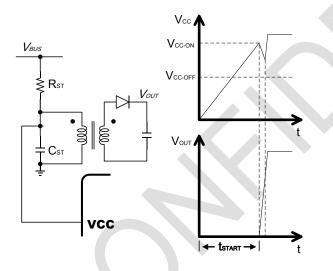


# FUNCTIONAL DESCRIPTION

SE8326 is a 4-Level Switch and PWM dimmable single stage Flyback and PFC controller for LED lighting applications. Primary side control is applied so that the system is simplified, and high power factor is achieved by constant on-time model. Boundary Conduction Mode (BCM) with valley switching improves efficiency and EMI performance. multi-protection The function stabilizes system and protects external components.

#### Startup

The capacitor  $C_{ST}$  across  $V_{BUS}$  and GND is charged by BUS through a start up resistor  $R_{ST}$  once BUS is powered on. After  $V_{CC}$  rises up to  $V_{CC-ON}$ , the internal blocks start to work and the gate driver begins to switch. Then  $V_{CC}$  will be pulled down by internal consumption until the power supply is taken over by the auxiliary winding.



#### Figure 3. Startup Sequence

In order that V can rise when start up, and fall when OVP and OTP,  $R_{ST}$  should be preset following this:

$$\frac{V_{BUS}}{I_Q} < R_{ST} < \frac{V_{BUS}}{I_{ST}}$$

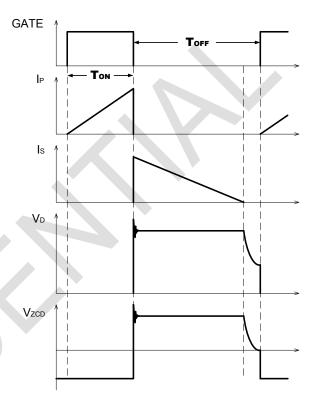
Select C<sub>ST</sub> for an ideal t<sub>ST</sub>:

$$t_{ST} = \frac{\frac{C_{ST}V_{BUS}}{\frac{V_{BUS}}{R_{ST}} - I_{ST}}$$

For a more stable  $V_{CC}$ , a bigger  $C_{ST}$  is needed, and  $R_{ST}$  should be decreased in order that  $t_{ST}$  is not changed. Obviously, the low  $I_{ST}$  of SE8326 makes it easier to design  $R_{ST}$ .

### BCM Operation

Boundary Conduction Mode (BCM) and valley switching provides low turn-on switching losses.



#### Figure 4. Boundary Conduction Mode

The voltage across drain and source of the external MOSFET is detected by the ZCD pin. The current of the inductor begins to decrease linearly as soon as the external MOSFET is turned off. When the current falls to zero, the MOSFET Drain-Source Voltage decreases, which is also detected by the ZCD pin through a resistor divider. The external MOSFET would be turned on by a turn on signal sent by the Zero Current Detector once the ZCD voltage is lower than 0.4V.

#### **DCM** Operation

Discontinuous Conduction Mode (DCM) is applied when COMP voltage is low. DCM can reduce the duty cycle down to less than 1%, and consequently a lower output current is obtained.



### FUNCTIONAL DESCRIPTION

### **Primary Side Constant Current Control**

The output mean current can be represented as

$$I_{OUT} = \frac{N \times 0.4V}{2R_{CS}}$$

N—The winding turns ratio of primary side to secondary side of the transformer.  $R_{CS}$ —The current sense resistor connected between the CS pin and GND.

### **Power Factor Correction**

Internal Constant On-Time Block affords a constant gate on-time  $T_{ON}$ , which is in proportion to COMP potential. The peak current of the primary side winding is

$$I_{\rm P} = \frac{T_{\rm ON}V_{\rm BUS}}{L_{\rm P}}$$

 $L_P$ —The primary inductance. As  $L_P$  and  $T_{ON}$  is constant,  $I_P$  is accordingly in proportion to  $V_{BUS}$  (as shown in Figure 5).

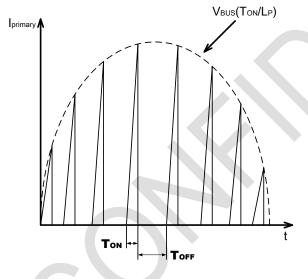


Figure 5. Power Factor Correction

As a result, the input current  $I_{IN}$  of the system follows the input voltage  $V_{IN}$ , and the Power Factor is improved.

### 4-Level Switch Dimming Control

SE8326 can implement 4-Level Switch Dimming function by internal dimming block and the external light switch. Figure 6 shows how 4-Level Switch Dimming works.

The first time switch turns on, the LED brightness is 100%. The brightness levels are traversed in an on-off manner if and only if the switch off time is

less than  $T_{DIM}$ . Once the off time is larger than  $T_{DIM}$ , then the brightness would be reset to 100%.

Different PWM pin settings choose different 4-Level Switch Dimming mods:

1. A 1nF cap connected to PWM pin chooses 100%, 50%, 20%, 5% and then back to 100% mod.

2. A 750k res connected to PWM pin chooses 100%, 50%, 25%, 12.5% and then back to 100% mod.

3. Setting PWM voltage lower than 2.5V (for example, connect to GND or input a 0 to 2V PWM signal) can abandon 4-Level Switch Dimming.

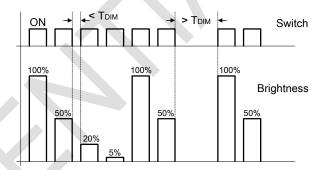


Figure 6. Dimming Function

### VCC Under-Voltage Lockout (UVLO)

When the V<sub>CC</sub> voltage drops below V<sub>CC-OFF</sub> (typically 8V), the whole chip shuts down, and GATE switching stops. The system would not work again until VCC capacitor is charged to V<sub>CC-ON</sub> through the external startup resistor.

### Auto Start

A auto start block is integrated in SE8326 to avoid unnecessary shut down. The auto start block starts timing as soon as the external MOSFET turns on in every period. If the ZCD pin fails to send a turn on signal after  $T_{START}$  (typically 140µs), the auto start block would turn on GATE automatically.

When the GATE is turned on, auto start timing stops.

### Minimum Off Time

To limit the maximum switching frequency and to obtain a better EMI performance, a internal block is integrated to limit the minimum GATE off time. The external MOSFET cannot turn on again in less than 3.6µs after its latest turning off.



# FUNCTIONAL DESCRIPTION

### Leading Edge Blanking (LEB)

An internal leading edge blanking (LEB) block is employed in order to avoid the premature termination of the GATE switching pulse due to the peak voltage of the CS pin caused by the parasitic capacitor discharging when the external MOSFET turns on.  $V_{CS}$  sampling is disabled during the LEB time.

### **Open-LED Protection**

When the load of the system is open, the output capacitor is charged up rapidly. As the voltage of the ZCD pin reflects the output voltage when the switch is on, the open-LED situation can be detected through the ZCD pin. Once ZCD voltage exceeds  $V_{OVP}$ , GATE would be shut down and the chip enters FAULT state, which would last until UVLO.

### Cycle-by-Cycle Over-Current Protection

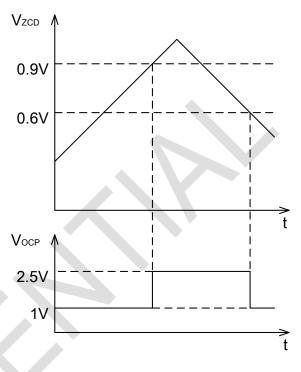
If the ZCD voltage in GATE on period is lower than 0.6V, the cycle-by-cycle current limit would be 1V. The current limit threshold voltage becomes up to 2.5V when the ZCD voltage in GATE on period is higher than 0.9V. Figure 6 shows this function. A lower OCP voltage can protect the external MOSFET as well as reduce power dissipation.

### **Short-Current Protection**

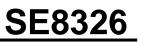
No output signal is fed back to the chip when the load is short, and consequently COMP voltage will rise rapidly. The chip enters FAULT state as soon as COMP reaches  $V_{OVP}$  (typically 4.4V).

### **Over-Temperature Protection (OTP)**

When the junction temperature is above 150°C, the chip enters FAULT state, and GATE driver is shut down. The UVLO signal can relive the system of FAULT state if the junction temperature drops below 125°C.

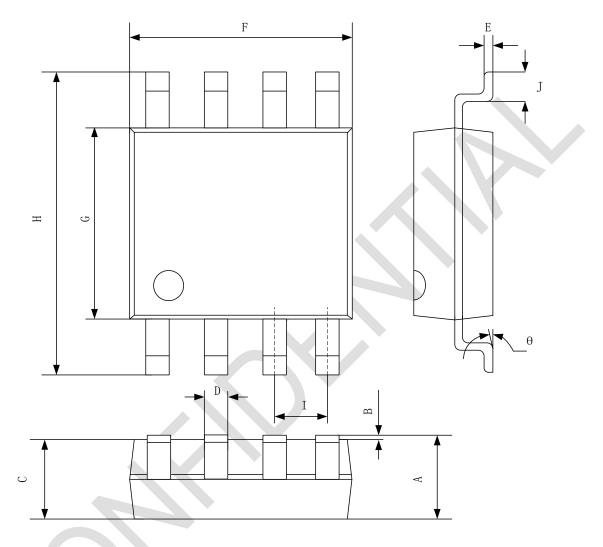






PACKAGE INFORMATION

SMET



| Symbol | Dimensions in Millimeters |       | Dimensions in Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
|        | Min                       | Max   | Min                  | Max   |  |
| A      | 1.350                     | 1.750 | 0.053                | 0.069 |  |
| В      | 0.100                     | 0.250 | 0.004                | 0.010 |  |
| С      | 1.350                     | 1.550 | 0.053                | 0.061 |  |
| D      | 0.330                     | 0.510 | 0.013                | 0.020 |  |
| E      | 0.170                     | 0.250 | 0.006                | 0.010 |  |
| F      | 4.700                     | 5.100 | 0.185                | 0.200 |  |
| G      | 3.800                     | 4.000 | 0.150                | 0.157 |  |
| Н      | 5.800                     | 6.200 | 0.228                | 0.244 |  |
| I      | 1.270                     | (BSC) | 0.050                | (BSC) |  |
| J      | 0.400                     | 1.270 | 0.400                | 1.270 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |



### SOLDERING INDICATION

This section gives a very brief insight to a complex technology. There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

### Reflow Soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stenciling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250°C. The top-surface temperature of the packages should preferable be kept below 220°C for thick/large packages, and below 235°C for small/thin packages.

#### Wave Soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used, the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch:

- larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;

- smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250°C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.



#### Manual Soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300°C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320°C.

### Suitability of Surface Mount IC Packages for Wave and Reflow Soldering Methods

| Package                                             | Soldering Method                  |                       |  |
|-----------------------------------------------------|-----------------------------------|-----------------------|--|
| Fachage                                             | Wave                              | Reflow <sup>(1)</sup> |  |
| BGA, HBGA, LFBGA, SQFP, TFBGA                       | Not suitable <sup>(2)</sup>       | Suitable              |  |
| HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, SMS | Not suitable                      | Suitable              |  |
| PLCC (3), SO, SOJ                                   | Suitable                          | Suitable              |  |
| LQFP, QFP, TQFP                                     | Not recommended <sup>(3)(4)</sup> | Suitable              |  |
| SSOP, TSSOP, VSO                                    | Not recommended <sup>(5)</sup>    | Suitable              |  |

#### Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect).
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch equal to or smaller than 0.5 mm.





Star Micro Electronic Technology Co.Ltd Room 602 UESTC Industrial Building NO.159, 1st Ring Rd, Chengdu, China Tel: (86) 28 8113 1361 Fax: (86) 28 8113 1841 Email: sales@star-micro.com Website: www.star-micro.com

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